

FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #16790HN

Generic Copy

Issue Date: 11-Dec-2014

<u>TITLE</u>: Final PCN for wafer fabrication site addition of ON Semiconductor Niigata Co. Ltd. in Niigata, Japan (Group HN)

PROPOSED FIRST SHIP DATE: Starting on 05-Apr-2015

AFFECTED CHANGE CATEGORY(S): Wafer Fabrication Site Addition

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or Yasuhiro.lgarashi@onsemi.com.

SAMPLES:

Contact your local ON Semiconductor Sales Office or <u>Shigehito.Matsumoto@onsemi.com</u>

ADDITIONAL RELIABILITY DATA:

Contact your local ON Semiconductor Sales Office or Kazutoshi.Kitazume@onsemi.com

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change. ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <u>quality@onsemi.com</u>

DESCRIPTION AND PURPOSE:

This is a Final Process Change Notification to announce the addition of a new wafer fabrication site for the devices covered in this notice. Devices formerly manufactured at the AMPI foundry site will also be manufactured at ON Semiconductor Niigata Co., Ltd. (OSNC) following the expiration of this notice. OSNC located in Niigata, Japan has obtained ISO9001 certification.

The product design and electrical specifications will remain identical. A full electrical characterization over the temperature range will be performed to check the device functionality and electrical specifications. Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.



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RELIABILITY DATA SUMMARY

Group HN Test: Steady State Operating Life High Temperature Reverse Bias Temp Humidity Storage Temperature Cycle Pressure Cooker High Temperature Storage	Conditions: Tj=150degC Ta=150degC, VDSS =max Ta=85degC, RH=85% Ta=-55degC to 150degC 30min each Ta=121degC,2.03×10°Pa,100% Ta=150degC	Interval: 1000 hrs 1000 hrs 1000 hrs 1000 cycles 50 hrs 1000 hrs	Results Pass Pass Pass Pass Pass Pass Pass
High Temperature Storage Resistance to Soldering heat (Ref	Ta=150degC low) Solder Temp.:260degC±5degC	1000 hrs 10s	Pass Pass
Solderability	Solder Temp.: 245degC±5degC	5 s	Pass

ELECTRICAL CHARACTERISTIC SUMMARY

There is no change in the electrical performance. Datasheet specifications remain unchanged.

CHANGED PART IDENTIFICATION

No change to current part marking will occur. Marking traceability codes will be able to identify wafer fab die source.

List of affected General parts:

Group HN

PART_ID
2SK4066-DL-1E
2SK4066-1E
2SK4094-1E